

# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

PUBLICATION NUMBER : 04074858  
 PUBLICATION DATE : 10-03-92

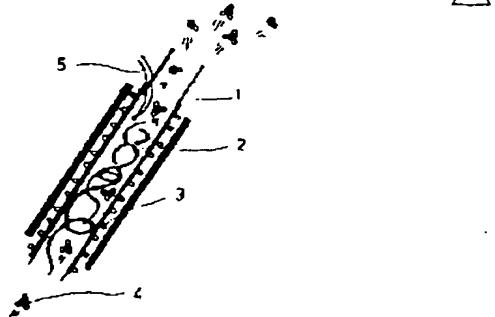
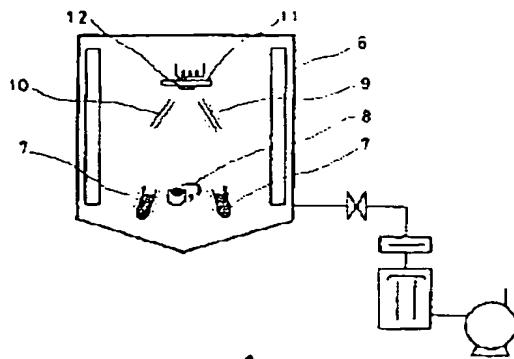
APPLICATION DATE : 16-07-90  
 APPLICATION NUMBER : 02185298

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INT.CL. : C23C 14/06 C01B 21/06 C23C 14/24  
 C23C 16/34 H01L 21/203 H01L 21/318

TITLE : PRODUCTION OF NITRIDE FILM



ABSTRACT : PURPOSE: To stably form a nitride film having a composition extremely close to stoichiometric composition on a substrate by heating and decomposing a gaseous nitrogen compound in vacuum in a cracking gas cell and generating highly active nitrogen.

CONSTITUTION: A substrate composed of Si, Al<sub>2</sub>O<sub>3</sub>, SiC, quartz glass, etc., as a substrate 12 to be filmed is fixed to a heater-containing holder 11 in a vacuum vessel 6, and a crucible 7 containing an element to be combined with N is disposed in the position opposite to the substrate 12 and the above element in the crucible 7 is heated and vaporized by electron beam, etc. A gaseous N compound, e.g., a gaseous matter of NH<sub>3</sub>, N<sub>2</sub>H<sub>4</sub>, N<sub>2</sub>H<sub>2</sub>, etc., is introduced into a cracking gas cell 9 and decomposed by heating with a heater 3 in the presence of a catalyst 2, such as Al<sub>2</sub>O<sub>3</sub> and Fe, in the inner part to produce N<sub>2</sub> gas having extremely high activity, and, a nitride film of BN, AlN, GaN, etc., formed by the reaction of this N<sub>2</sub> gas with the gas of element, such as B, Al, and Ga, produced from the crucible 7 can be formed on the surface of the substrate 12.

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